

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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High Voltage Transistor

PNP Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-150	Vdc
Collector - Base Voltage	V _{CBO}	-160	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) T _A = 25°C Derate Above 25°C	P _D	225	mW mW/°C
Derate Above 25°C		1.8	mvv/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C	P _D	300	mW
Derate Above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

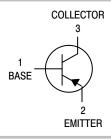


ON Semiconductor®

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SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



2L = Specific Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
NSVMMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-150	_	Vdc
Collector – Base Breakdown Voltage ($I_C = -100 \mu Adc, I_E = 0$)	V _{(BR)CBO}	-160	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	_	Vdc
Collector–Base Cutoff Current $(V_{CB} = -120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	I _{CBO}	- -	-50 -50	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain $ \begin{aligned} &(I_C = -1.0 \text{ mAdc, } V_{CE} = -5.0 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc, } V_{CE} = -5.0 \text{ Vdc}) \\ &(I_C = -50 \text{ mAdc, } V_{CE} = -5.0 \text{ Vdc}) \end{aligned} $	h _{FE}	50 60 50	_ 240 _	-
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	- -	-0.2 -0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	V _{BE(sat)}	- -	-1.0 -1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain — Bandwidth Product (I _C = -10 mAdc, V _{CE} = -10 Vdc, f = 100 MHz)	f _T	100	300	MHz
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{obo}	_	6.0	pF
Small Signal Current Gain ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	h _{fe}	40	200	-
Noise Figure (I _C = $-200~\mu$ Adc, V _{CE} = $-5.0~V$ dc, R _S = $10~\Omega$, f = $1.0~k$ Hz)	NF	_	8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

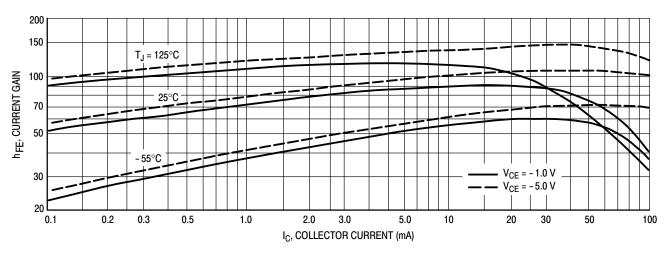


Figure 1. DC Current Gain

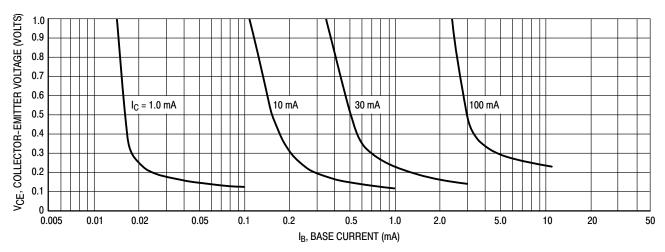


Figure 2. Collector Saturation Region

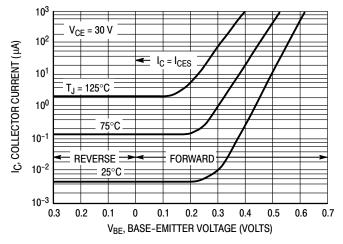


Figure 3. Collector Cut-Off Region

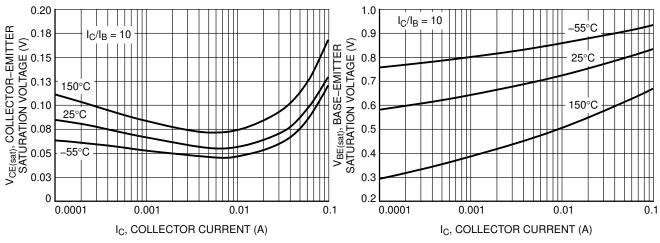


Figure 4. Collector Emitter Saturation Voltage vs. Collector Current

Figure 5. Base Emitter Saturation Voltage vs. Collector Current

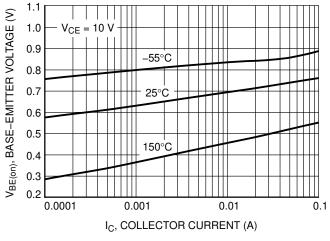


Figure 6. Base Emitter Voltage vs. Collector Current

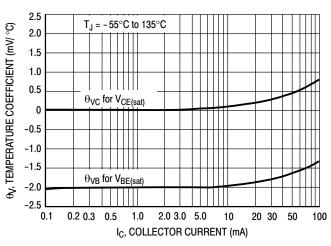


Figure 7. Temperature Coefficients

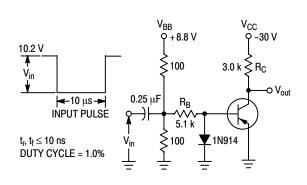


Figure 8. Switching Time Test Circuit

Values Shown are for I_C @ 10 mA

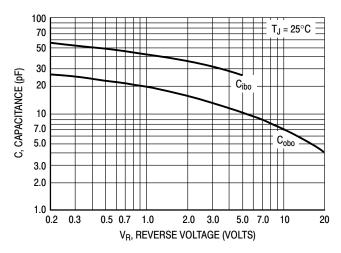
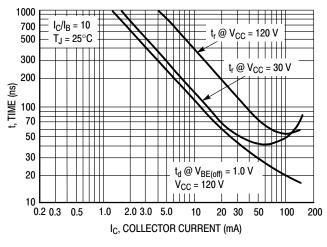


Figure 9. Capacitances



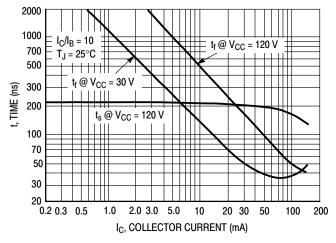
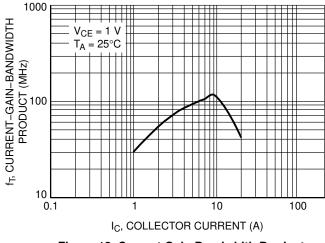
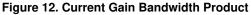


Figure 10. Turn-On Time

Figure 11. Turn-Off Time





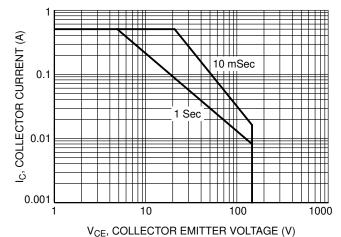
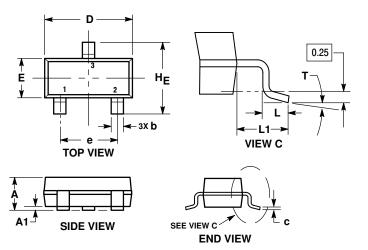


Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

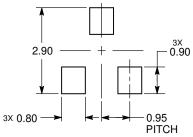
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 6:

PIN 1. BASE **EMITTER**

COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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